

**1. Material**  
 Substrate GaAs (N Type)  
 Epitaxial Layer GaAlAs (P/N Type)

**2. Electrode**  
 N(Cathode) Side Gold Alloy  
 P(Anode) Side Gold Alloy

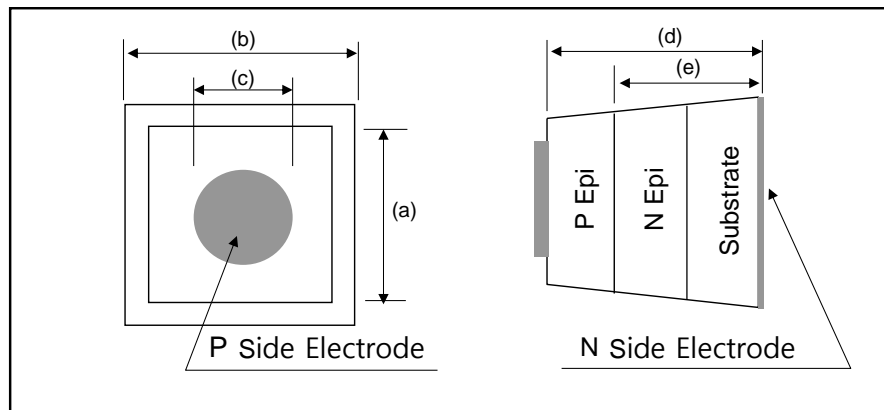
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$			1.6	V	IF=100mA
Reverse Voltage	$V_R$	10			V	IR=0.1uA
Power	$P_O$	25			mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=100mA
	$\Delta\lambda$		55		nm	IF=100mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

(a) Emission Area	-----	11.0mil x 11.0mil
(b) Bottom Area	-----	12.0mil x 12.0mil
(c) Bonding Pad	-----	130um
(d) Chip Thickness	-----	9mil
(e) Junction Height	-----	4.7mil



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